



PJP70N10L

100V N-Channel Enhancement Mode MOSFET

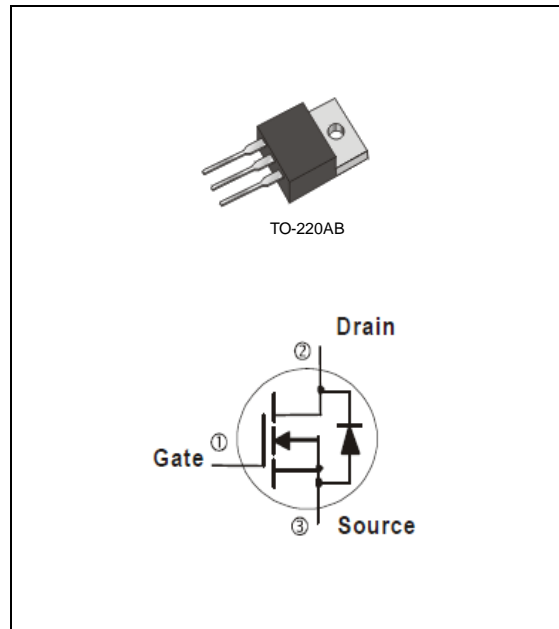
Voltage 100 V **Current** 70 A

Features

- $R_{DS(ON)}$, $V_{GS}@10V, I_D@20A < 12m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

- Case : TO-220AB Package
- Terminals : Solderable per MIL-STD-750, Method 2026



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 25	V
Continuous Drain Current	$T_C=25^\circ\text{C}$	I_D	70	A
	$T_C=100^\circ\text{C}$		50	
Pulsed Drain Current ^(Note 1)	$T_C=25^\circ\text{C}$	I_{DM}	280	
Power Dissipation	$T_C=25^\circ\text{C}$	P_D	166	W
	$T_C=100^\circ\text{C}$		83	
Single Pulse Avalanche Energy ^(Note 5)		E_{AS}	225	mJ
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~175	$^\circ\text{C}$
Typical Thermal Resistance				$^\circ\text{C/W}$
-	Junction to Case	$R_{\theta JC}$	0.9	
-	Junction to Ambient	$R_{\theta JA}$	62.5	

- Limited only By Maximum Junction Temperature



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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	2.94	4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	9.4	12	m Ω
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V$	-	-	1.0	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 25V, V_{DS}=0V$	-	-	± 100	nA
Dynamic (Note 7)						
Total Gate Charge	Q_g	$V_{DS}=50V, I_D=30A,$ $V_{GS}=10V$ (Note 1,2)	-	69	-	nC
Gate-Source Charge	Q_{gs}		-	9.8	-	
Gate-Drain Charge	Q_{gd}		-	27	-	
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0\text{MHz}$	-	3061	-	pF
Output Capacitance	C_{oss}		-	366	-	
Reverse Transfer Capacitance	C_{rss}		-	187	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=50V, I_D=30A,$ $V_{GS}=10V, R_G=6.8\Omega$ (Note 1,2)	-	25	-	ns
Turn-On Rise Time	t_r		-	66	-	
Turn-Off Delay Time	$t_{d(off)}$		-	76	-	
Turn-Off Fall Time	t_f		-	46	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S	---	-	-	70	A
Diode Forward Voltage	V_{SD}	$I_S=20A, V_{GS}=0V$	-	0.84	1.3	V
Reverse Recovery Time	t_{rr}	$V_{GS}=0V, I_S=30A$	-	46	-	nS
Reverse Recovery Charge	Q_{rr}	$di_F/dt=100A/\mu s$ (Note 2)	-	88	-	nC

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature $T_J(\text{MAX})=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.
4. The maximum current rating is package limited.
5. The test condition is $L=0.5\text{mH}, I_{AS}=30A, V_{DD}=25V, V_{GS}=10V$
6. Guaranteed by design, not subject to production testing.



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TYPICAL CHARACTERISTIC CURVES

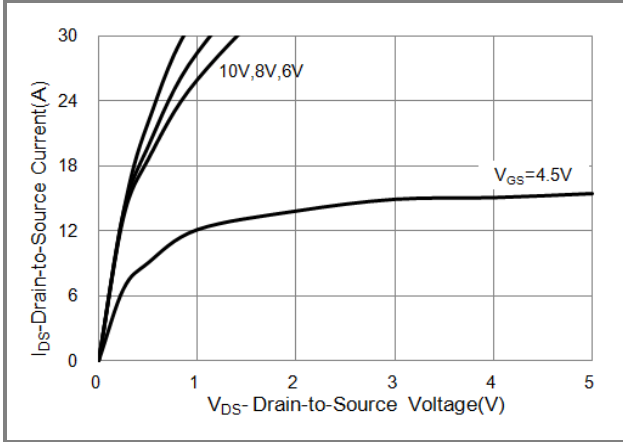


Fig.1 Output Characteristics

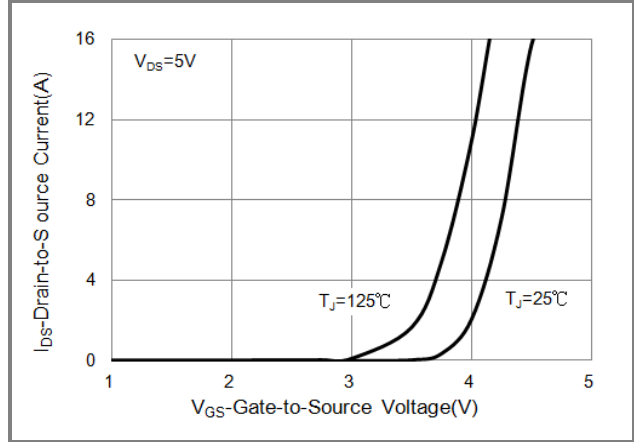


Fig.2 Transfer Characteristics

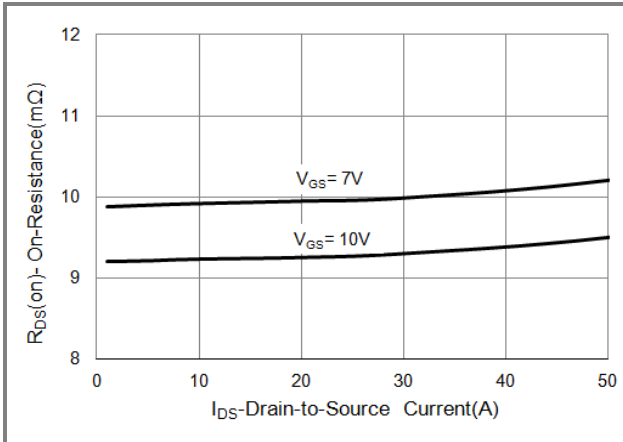


Fig.3 On-Resistance vs. Drain Current

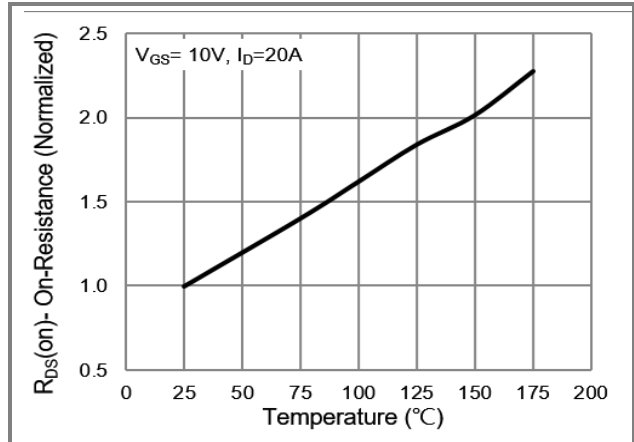


Fig.4 On-Resistance vs. Junction temperature

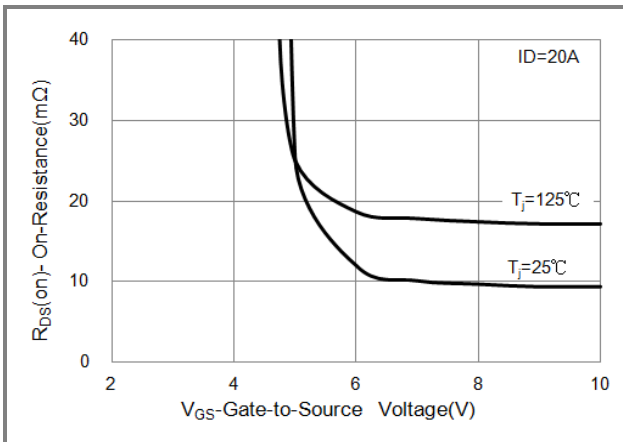


Fig.5 On-Resistance Variation with VGS.

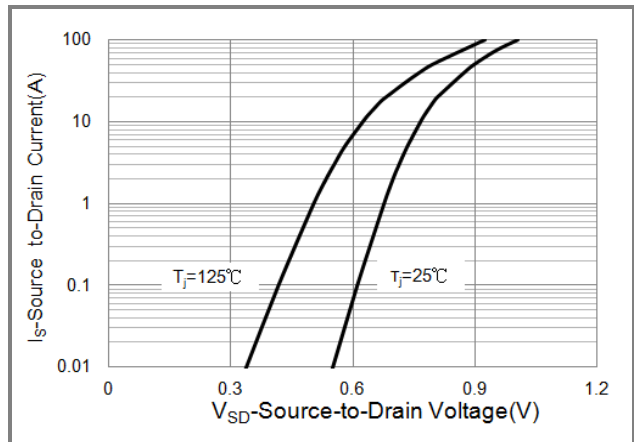


Fig.6 Source-Drain Diode Forward Voltage



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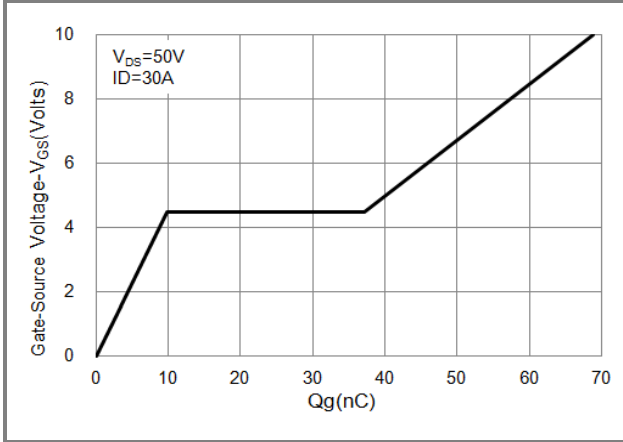


Fig.7 Gate-Charge Characteristics

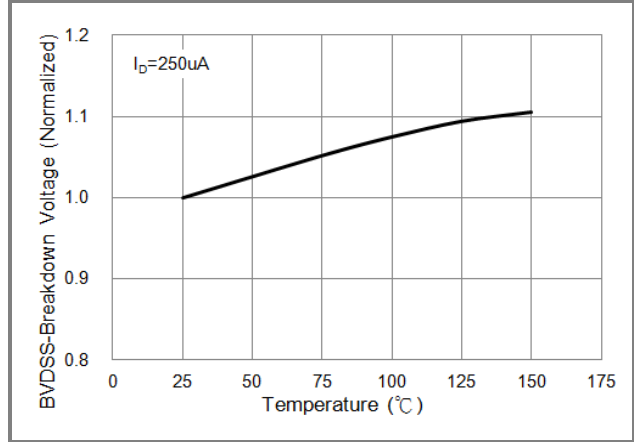


Fig.8 Breakdown Voltage Variation vs. Temperature

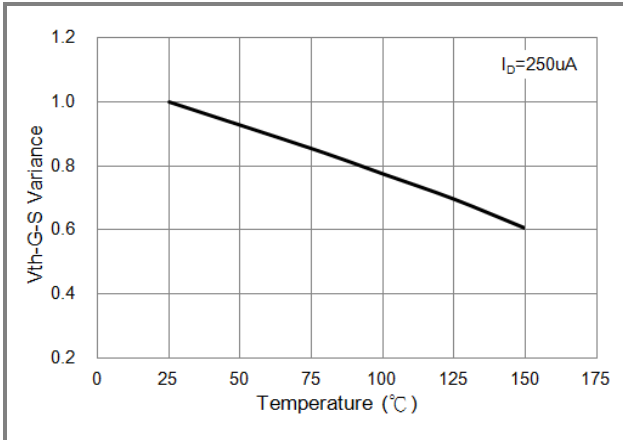


Fig.9 Threshold Voltage Variation with Temperature

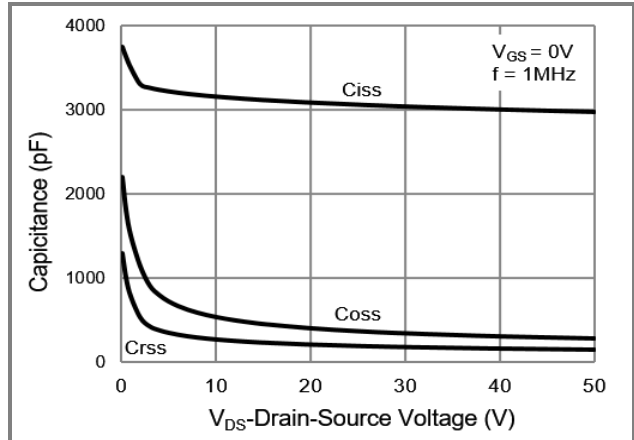


Fig.10 Capacitance vs. Drain-Source Voltage

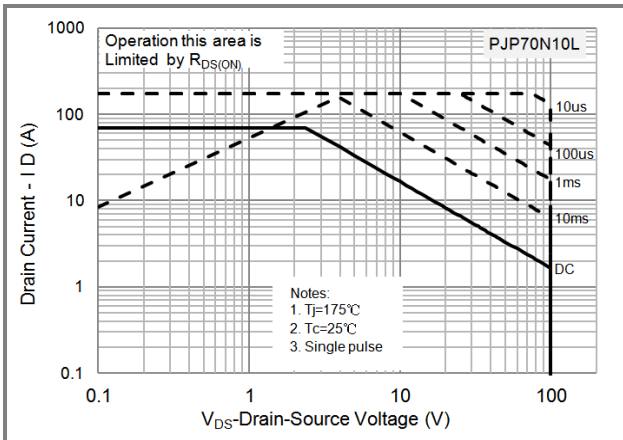


Fig.11 Maximum Safe Operating Area



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TYPICAL CHARACTERISTIC CURVES

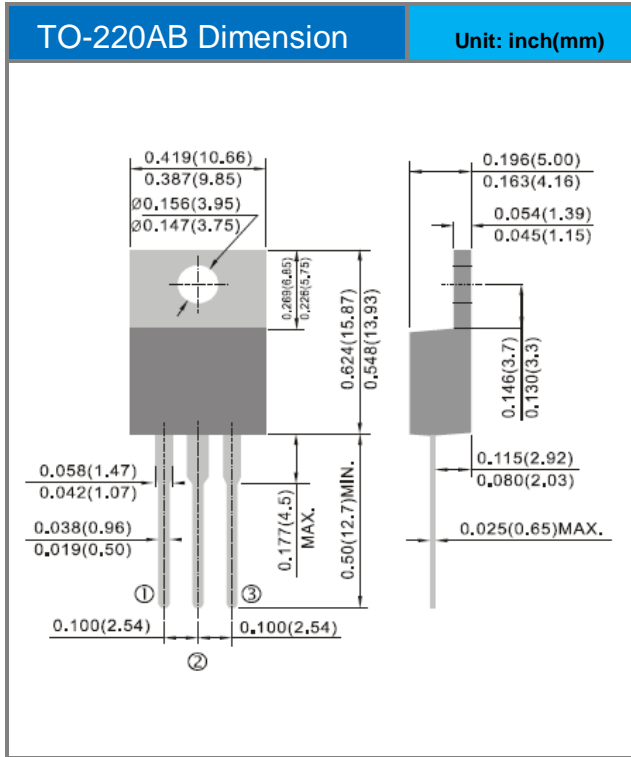


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width



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Packaging Information





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PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJP70N10L_TO_00001	TO-220AB	50pcs / Tube	P70N10L	Halogen free



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